

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3396738	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 10:54
L2	3968	1 and cell with select\$5 adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 10:56
L3	290	2 and eras\$5 with (block or sector or bank or subarray) with (potential or voltage or level) with (bit or bitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 11:08
L4	4	3 and high adj voltage adj transistor with eras\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 10:59
L5	9	3 and transistor with (block or bank or sector or group or subarray) with column adj select\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 11:09

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((memory or storage) and unit and cell and select adj gate adj transistors and eras\$5 and set\$5 and (voltage or potential or level) and (block or bank or sector) and high adj voltage adj transistor and column adj select\$5).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 16:15
L2	0	((memory or storage) and unit and cell and select adj gate adj transistors and eras\$5 and (voltage or potential or level) and (block or bank or sector) and high adj voltage adj transistor and column adj select\$5).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 16:15
L3	0	((memory or storage) and cell and select adj gate adj transistors and eras\$5 and (voltage or potential or level) and (block or bank or sector) and high adj voltage adj transistor and column adj select\$5).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 16:15
L4	1	((memory or storage) and cell and select adj gate adj transistors and eras\$5 and (voltage or potential or level) and (block or bank or sector) and transistor and column adj select\$5).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/30 16:15